

N-Channel Field Effect Transistor

12N035

Description

The Bay Linear n-channel power field effect transistors are produced using high cell density DMOS technology, These devices are particularly suited for low voltage applications such as automotive and other battery powered circuits where fast switching, low in-line power loss and resistance to transistors are needed.

The TO-220 is offered in a 3-pin is universally preferred for all commercial-industrial applications at power dissipation level to approximately to 50 watts. Also, available in a D^2 surface mount power package with a power dissipation up to 2 Watts



Features

- Critical DC Electrical parameters specified at elevated Temp.
- Rugged internal source-drain diode can eliminate the need for external Zener diode transient suppresser
- Super high density cell design for extremely low R_{DS(ON)}

$$\begin{split} V_{\rm DSS} &= 30V \\ R_{\rm DS~(ON)} &= 0.045~\Omega \\ I_D &= 12A \end{split}$$

Ordering Information

Device	Package	Temp.
12N035T	TO-220	0 to 150°C
12N035S	$TO-263 (D^2)$	0 to 150°C

Absolute Maximum Rating

Symbol	Parameter	Max	Unit	
I _D	Drain Current			
	-Continues	12	Α	
	-Pulsed	36		
V _{DSS}	Drain-Source Voltage	30	V	
V _{GSV}	Gate Source Voltage	±20	V	
P _D	Total Power Dissipation @ T _C =25°C	50	W	
	Derate above 25°C	0.4	W/°C	
T _J	Operating and Storage -65 to 175		90	
T _{STG}	Temperature Range		°C	



Symbol	Parameter	Conditions	Min	Тур	Max	Units				
OFF CHAF	OFF CHARACTERSTICS									
BV _{DSS}	Drain source breakdown voltage	V _{GS} =0V, I _D =250µA	30			V				
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V V _{GS} =0V			10	μA				
I _{GBLF}	Gate-Body Leakage Forward	$V_{GS}=20V$ $V_{DS}=0V$			100	nA				
I _{GBLR}	Gate-Body Leakage Reverse	V_{GS} =-20V V_{DS} =0V			-100	nA				
ON CHAR	ACTERSTICS									
V _{GS(TH)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	1		3	v				
R _{DS(ON)}	Static Drain Voltage	V _{GS} =10V, I _D =26A V _{CS} =4.5V, I _O =21A			0.045 0.06	Ω				
I _{D(ON)}	ON-State Drain Current	V _{GS} =10V	12			Α				
g _{fs}	Forward Tranconductance	$V_{DS}=10V, I_D=6A$		9		S				
	CHARACTRISTICS									
C _{ISS}	Input Capacitance	$\mathbf{V} = 10\mathbf{V} \mathbf{V} = 0\mathbf{V}$			550	pF				
Coss	Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V$ F=1.0 MHZ			300	pF				
C _{RSS}	Reverse Tras. Capacitance				150	pF				
SWITCHIN	NG CHARACTERSTICS									
t _{D(ON)}	Turn-ON Delay Time	V _{DD} =10V			16	nS				
t _r	Turn-ON Rise Time	$I_{D}=12A, V_{DS}=10V$			250					
t _{d(off)}	Turn-OFF Delay Time	$R_{GEN}=24\Omega$			90					
t _F	Turn-OFF Fall Time				200					
	PRAIN DIODE CHRACTERIS									
Is	Maxim Continuous Drain sour				12	Α				
V _{DS} (note)	Drain Source Diode Forward Voltage	V _{GS} =0V I _S =6A			1.30	V				
THERMAI	CHRACTERISTICS	·	· ·							
R _{JC}	Thermal Resistance, Junction to Case			5	°C/W					
R _{JC}	Thermal Resistance, Junction to Ambient				100	°C/W				

Electrical Characteristics (T_C = 25°C unless otherwise specified)

Note: Pulse Test: Pulse With $\leq 300 \ \mu$ S, Duty Cycle $\leq 2.0\%$

Advance Information- These data sheets contain descriptions of products that are in development. The specifications are based on the engineering calculations, computer simulations and/ or initial prototype evaluation.

Preliminary Information- These data sheets contain minimum and maximum specifications that are based on the initial device characterizations. These limits are subject to change upon the completion of the full characterization over the specified temperature and supply voltage ranges.

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